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Harada et al.

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(54)	SEMICONDUCTOR INTEGRATED CIRCUIT DEVICE HAVING DOUBLE DIFFUSION INSULATED GATE FIELD EFFECT TRANSISTOR				
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(58)	<b>Field of Search</b>				
(56)	References Cited				

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## (57) ABSTRACT

To provide a lateral double diffusion insulated gate field effect transistor with high driving current and low source-drain withstand voltage without receiving the influence of process fluctuation. Without shortening a gate electrode 10 as compared with conventional one, an impurity of the same conductivity type as a drain is ion-implanted from the side of a high concentration drain region 20 by using the gate electrode as a mask in a self-aligning manner. The amount of impurity implantation is set as higher than the concentration of a semiconductor substrate 19.

## 14 Claims, 5 Drawing Sheets

